NTR5198NL

Power MOSFET

60 V, 155 mΩ, Single N−Channel Logic Level, SOT−23

Features

- Small Footprint Industry Standard Surface Mount SOT−23 Package
- Low $R_{DS(on)}$ for Low Conduction Losses and Improved Efficiency
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	60	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\Psi J-mb}$ (Notes 1, 2, 3, and 4)	Steady State	T_A = 25°C	I_D	2.2	A
		T_A = 100°C		1.6	
Power Dissipation $R_{\Psi J-mb}$ (Notes 1 and 3)		T_A = 25°C	P_D	1.5	W
		T_A = 100°C		0.6	
Continuous Drain Current $R_{\theta JA}$ (Note 1, 2, 3, and 4)	Steady State	T_A = 25°C	I_D	1.7	A
		T_A = 100°C		1.2	
Power Dissipation $R_{\theta JA}$ (Notes 1 and 3)		T_A = 25°C	P_D	0.9	W
		T_A = 100°C		0.4	
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	27	A
Operating Junction and Storage Temperature			T_J, T_{stg}	−55 to 150	°C
Source Current (Body Diode)			I_S	1.9	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Psi (Ψ) is used as required per JESD51−12 for packages in which substantially less than 100% of the heat flows to single case surface.
3. Surface−mounted on FR4 board using a 650 mm2, 2 oz. Cu pad.
4. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

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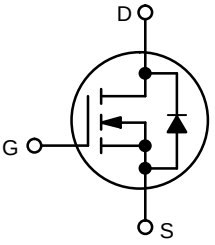
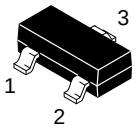
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
60 V	155 mΩ @ 10 V	2.2 A
	205 mΩ @ 4.5 V	

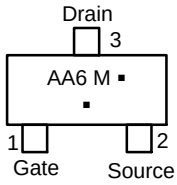
N−Channel





SOT−23
CASE 318
STYLE 21

MARKING DIAGRAM/ PIN ASSIGNMENT



AA6 = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NTR5198NLT1G	SOT−23 (Pb−Free)	3000 / Tape & Reel
NTR5198NLT3G	SOT−23 (Pb−Free)	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction−to−Lead #3 − Drain (Notes 2 and 3)	$R_{\Psi J-mb}$	86	°C/W
Junction−to−Ambient − Steady State (Note 3)	$R_{\theta JA}$	139	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		60			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	Reference to 25°C, I_D = 250 μA			70		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 60 V	T_J = 25°C			1.0	μA
			T_J = 125°C			10	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250 μA		1.5		2.5	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	Reference to 25°C, I_D = 250 μA			−6.5		mV/°C
Drain−to−Source On−Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 1 A			107	155	mΩ
		V_{GS} = 4.5 V, I_D = 1 A			142	205	
Forward Transconductance	g_{FS}	V_{DS} = 5.0 V, I_D = 1 A			3		S
CHARGES, CAPACITANCES & GATE RESISTANCE							
Input Capacitance	C_{iss}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = 25 V			182		pF
Output Capacitance	C_{oss}				25		
Reverse Transfer Capacitance	C_{rss}				16		
Total Gate Charge	$Q_{G(TOT)}$	V_{DS} = 48 V, I_D = 1 A	V_{GS} = 4.5 V		2.8		nC
			V_{GS} = 10 V		5.1		
Threshold Gate Charge	$Q_{G(TH)}$	V_{DS} = 48 V, I_D = 1 A V_{GS} = 10 V			0.3		
Gate−to−Source Charge	Q_{GS}				0.8		
Gate−to−Drain Charge	Q_{GD}				1.5		
Plateau Voltage	V_{GP}				3.1		V
Gate Resistance	R_G				8		Ω
SWITCHING CHARACTERISTICS (Note 6)							
Turn−On Delay Time	$t_{d(on)}$	V_{DS} = 30 V, V_{GS} = 10 V, I_D = 1 A, R_G = 10 Ω			5		ns
Rise Time	t_r				7		
Turn−Off Delay Time	$t_{d(off)}$				13		
Fall Time	t_f				2		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 1 A	T_J = 25°C		0.8	1.2	V
			T_J = 125°C		0.6		
Reverse Recovery Time	t_{rr}	I_S = 1 A_{dc}, V_{GS} = 0 V_{dc}, dI_S/dt = 100 A/μs			12		ns
Charge Time	t_a				9		
Discharge Time	t_b				3		
Reverse Recovery Stored Charge	Q_{RR}				6		nC

5. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

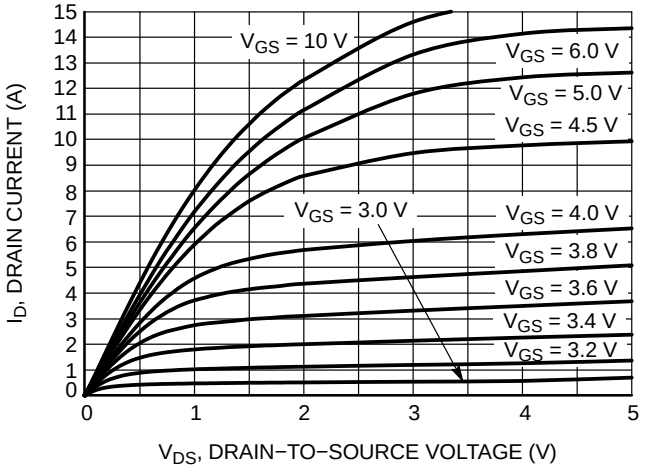


Figure 1. On−Region Characteristics

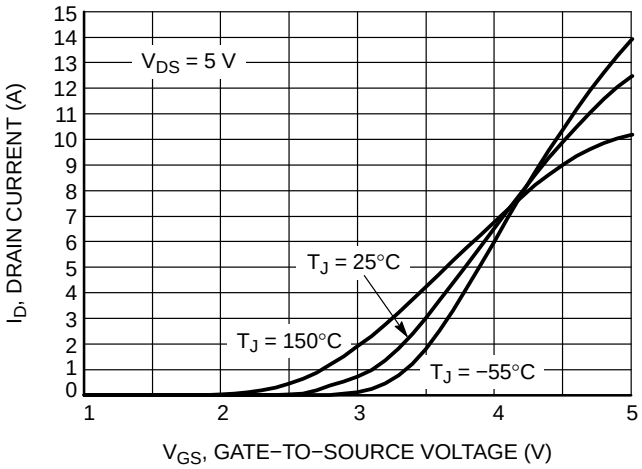


Figure 2. Transfer Characteristics

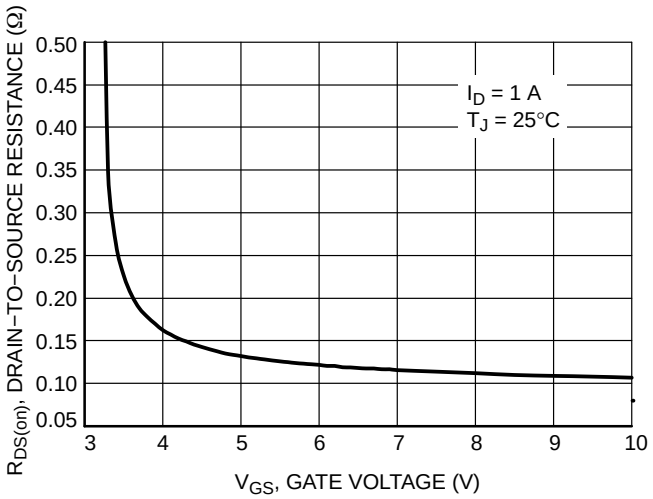


Figure 3. On−Resistance vs. Gate−to−Source Voltage

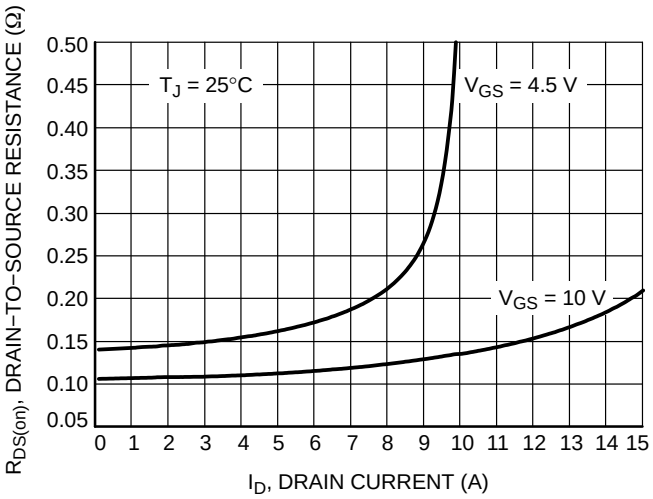


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

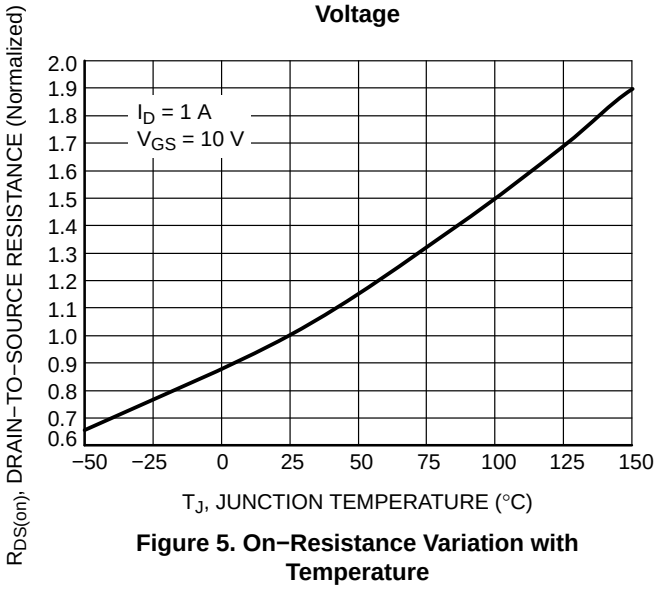


Figure 5. On−Resistance Variation with Temperature

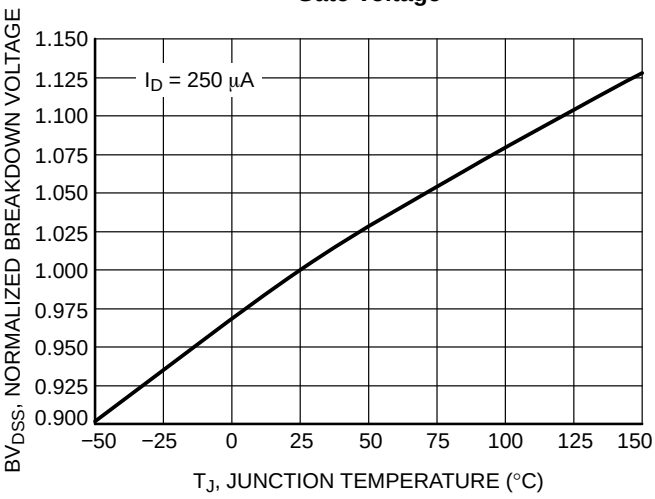


Figure 6. Breakdown Voltage Variation with Temperature

TYPICAL CHARACTERISTICS

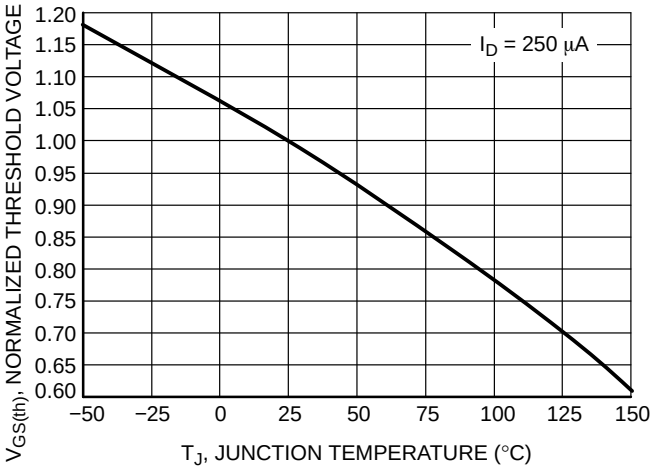


Figure 7. Threshold Voltage Variation with Temperature

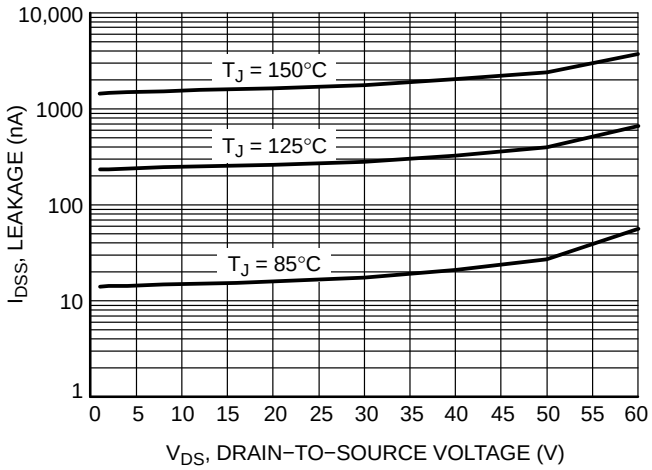


Figure 8. Drain−to−Source Leakage Current vs. Voltage

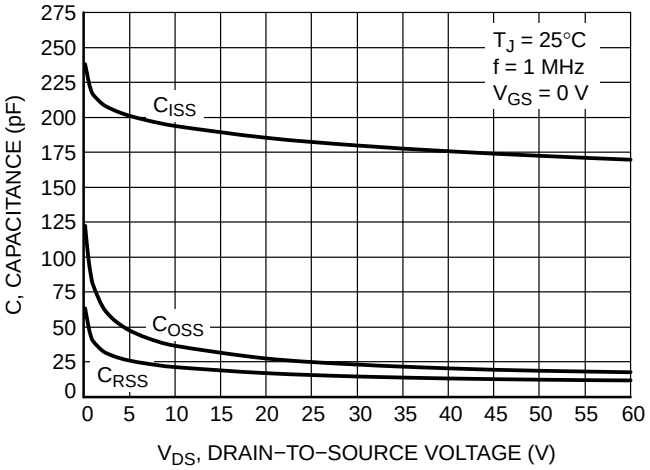


Figure 9. Capacitance Variation

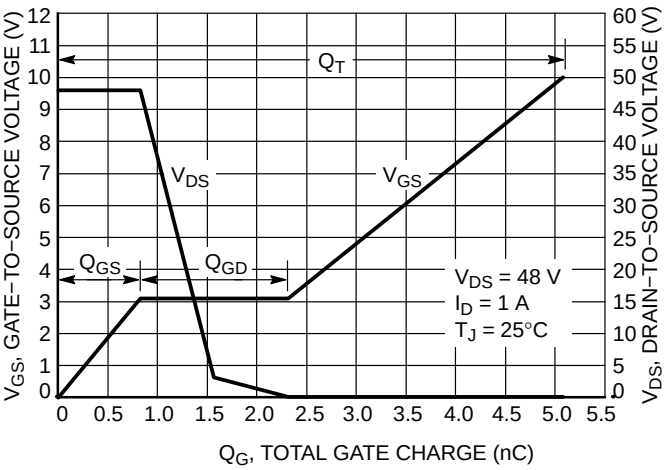


Figure 10. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

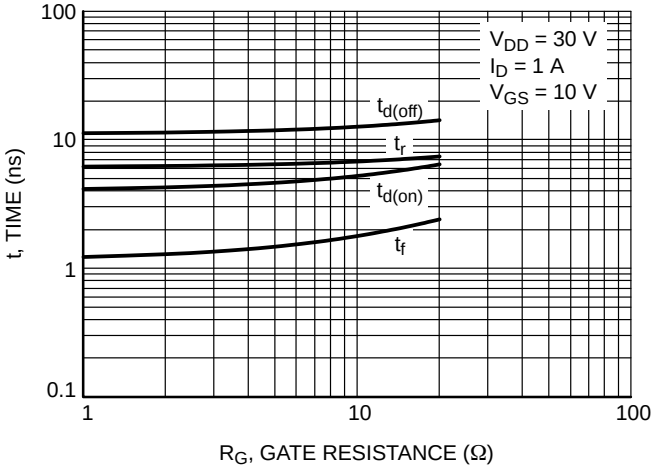


Figure 11. Resistive Switching Time Variation vs. Gate Resistance

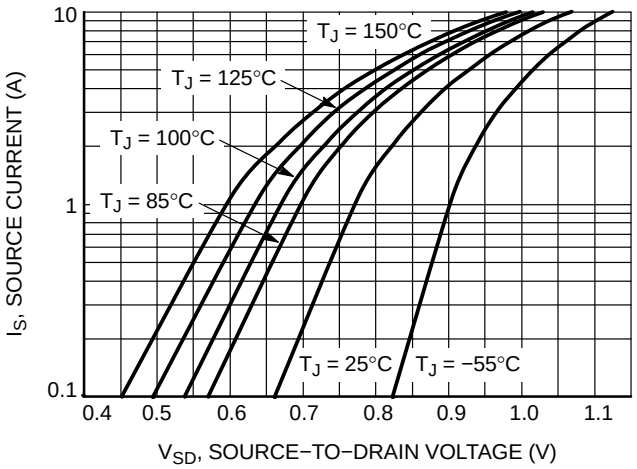


Figure 12. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS

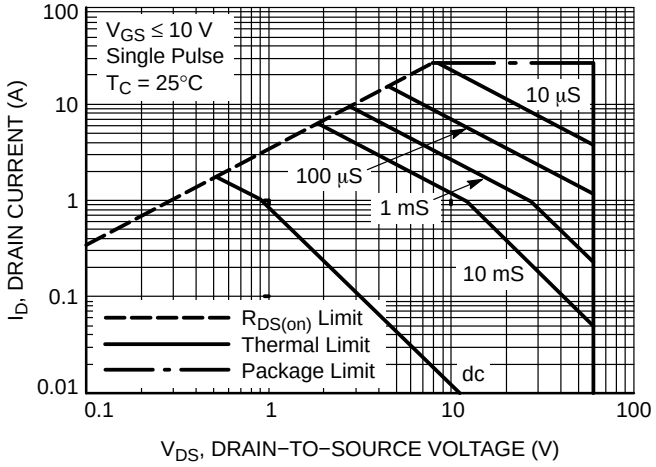


Figure 13. Maximum Rated Forward Biased Safe Operating Area

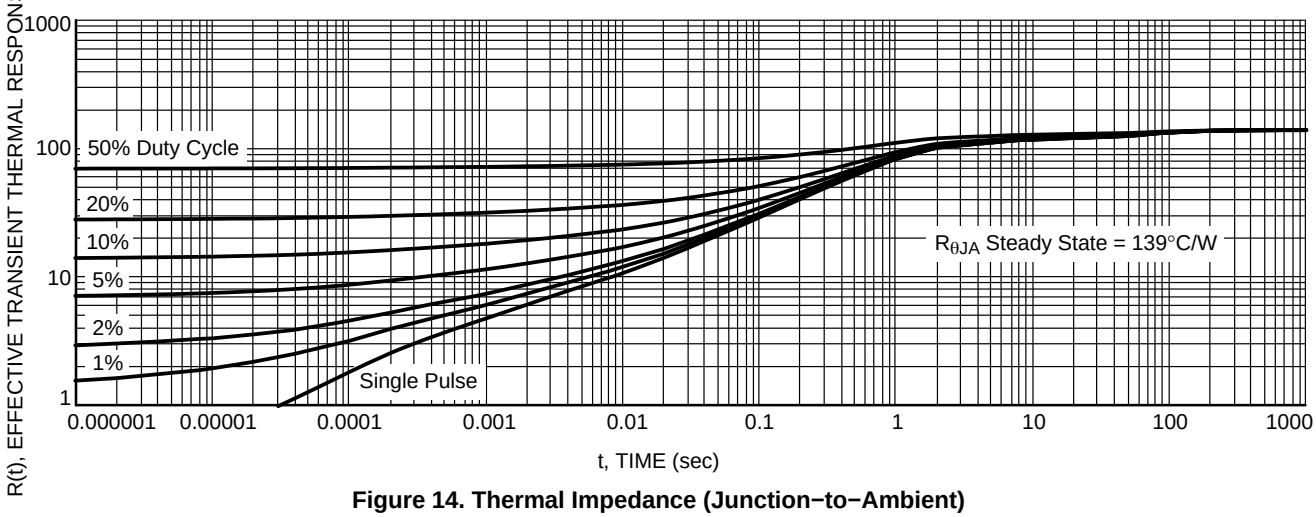
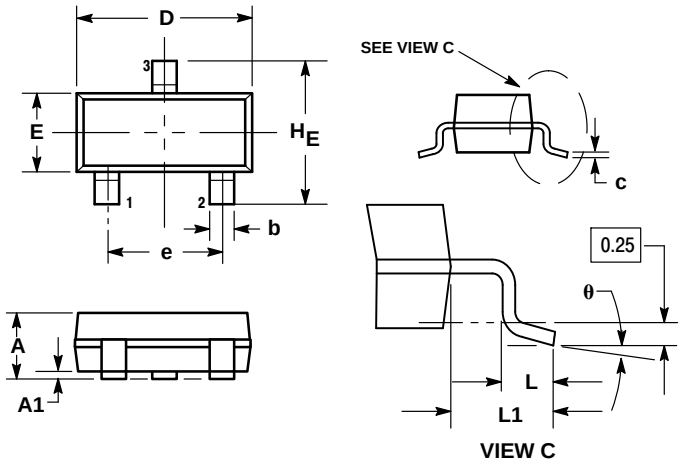


Figure 14. Thermal Impedance (Junction−to−Ambient)

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AP

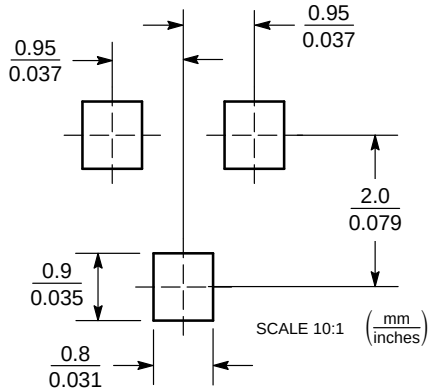


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	−−−	10°	0°	−−−	10°

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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